METHOD FOR FABRICATING DEVICE STRUCTURES HAVING A VARIATION IN ELECTRICAL CONDUCTIVITY

ABSTRACT

A method for forming device structures having a variation in electrical conductivity includes forming a device structure and a radiation absorbing layer overlying the device structure. The radiation absorbing layer has a spatial variation and radiation absorbing characteristics, such that upon irradiating the device structure, the radiation absorbing layer attenuates the intensity of the radiation so that a variation in dopant activation takes place within the device structure. Accordingly, device structures are formed having a variation in electrical resistance independent of the physical size of the device structures.

Figure 6